Abstracts

A 30 GHz Low Noise FET Amplifier

E.T. Watkins, J.M. Schellenberg and H. Yamasaki. "A 30 GHz Low Noise FET Amplifier." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 321-323.

A low noise FET amplifier has been developed for the 27.5 to 30 GHz communications band using a new 1/4 m gate GaAs FET device. The 3-stage amplifier exhibits a maximum noise figure of 3.2 dB across the 27.5 to 30 GHz band with an associated gain of 23 ±0.5 dB.

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